



PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of

Hiroyuki ABE et al.

Application No.: 08/930,449

Filed: October 7, 1997

For: HIGH ENERGY SUPPLY APPARATUS, METHOD OF
FORMING CRYSTALLINE FILM AND METHOD OF
MANUFACTURING THIN FILM ELECTRONIC DEVICE

Group Art Unit: 2814

Examiner: S. Rao

Docket No.: JAO 39514

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11/26/01
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AMENDMENT

Director of the U.S. Patent and Trademark Office
Washington, D.C. 20231

Sir:

In reply to the Office Action mailed July 18, 2001, please amend the application as follows.

IN THE CLAIMS:

Please replace claims 20, 25 and 46 as follows:

20. (Four Times Amended) A method of forming a crystalline film, comprising:
- forming a thin film on a substrate;
- setting the thin film in a supply chamber of a high energy supply apparatus including a generation source for generating the high energy and the supply chamber for supplying the high energy to the thin film, the supply chamber including an introduction window that introduces the high energy into the supply chamber;
- crystallizing at least a surface layer of the thin film by supplying high energy to the thin film under a hydrogen-containing atmosphere, at least the surface layer of the thin film being melted by the high energy and crystallized by cooling solidification, and unpaired

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